Contribution ID: 13 Type: not specified

TCAD simulation of Si crystal with different clusters.

Wednesday 17 November 2010 14:30 (20 minutes)

The TCAD Synopsis program was used for: 1) investigation of electric field distribution in Si crystal containing different types and concentration of clusters; 2) analysis of dynamics of electric field around the cluster during and after excitation by a short light pulse. An aim of presentation is an attraction of proposals to model the behavior of semiconductor in other situations.

Author: Prof. VAITKUS, Juozas (Vilnius University)

Co-authors: Dr ZASINAS, Ernestas (Vilnius university); Mr BONDZINSKAS, Rokas (Vilnius university)

Presenter: Prof. VAITKUS, Juozas (Vilnius University)

Session Classification: Defect and Material Characterization